

Features

- Enhancement mode
- VitoMOS® II Technology
- Fast Switching and High efficiency
- 100% Avalanche test

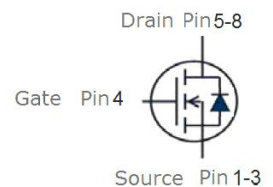
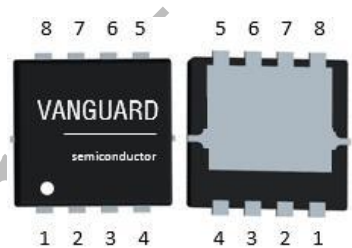
V_{DS}	40	V
$R_{DS(on), Typ@ V_{GS}=10V}$	6.4	mΩ
$R_{DS(on), Typ@ V_{GS}=4.5V}$	10	mΩ
I_D	54	A



Halogen-Free

Part ID	Package Type	Marking	Packing
VS4620GEMC	PDFN3333	4620GE	5000PCS/Reel

PDFN3333



Maximum ratings, at $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	40	V
V_{GS}	Gate-Source voltage	± 20	V
I_S	Diode continuous forward current	$T_C = 25^\circ\text{C}$	A
I_D	Continuous drain current @ $V_{GS}=10V$	$T_C = 25^\circ\text{C}$	54
		$T_C = 100^\circ\text{C}$	34
I_{DM}	Pulse drain current tested ①	$T_C = 25^\circ\text{C}$	216
I_{DSM}	Continuous drain current @ $V_{GS}=10V$	$T_A = 25^\circ\text{C}$	19
		$T_A = 70^\circ\text{C}$	15
E_{AS}	Avalanche energy, single pulsed ②	20	mJ
P_D	Maximum power dissipation	$T_C = 25^\circ\text{C}$	30
		$T_C = 100^\circ\text{C}$	12
P_{DSM}	Maximum power dissipation ③	$T_A = 25^\circ\text{C}$	3.6
		$T_A = 70^\circ\text{C}$	2.3
$T_{STG, TJ}$	Storage and Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.2	5.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	35	42	$^\circ\text{C/W}$

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T _j =25°C (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	45	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _j =125°C)	V _{DS} =40V, V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.1	1.65	2.3	V
R _{DS} (on)	Drain-Source On-State Resistance ④	V _{GS} =10V, I _D =20A	--	6.4	8.3	mΩ
		T _j =100°C	--	7.8	--	mΩ
R _{DS} (on)	Drain-Source On-State Resistance ④	V _{GS} =4.5V, I _D =10A	--	10	13	mΩ
Dynamic Electrical Characteristics @ T _j = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1MHz	550	735	980	pF
C _{oss}	Output Capacitance		215	285	380	pF
C _{rss}	Reverse Transfer Capacitance		15	25	60	pF
R _g	Gate Resistance	f=1MHz	0.2	1.7	5	Ω
Q _g (10V)	Total Gate Charge	V _{DS} =20V, I _D =20A, V _{GS} =10V	--	15	--	nC
Q _g (4.5V)	Total Gate Charge		--	7.6	--	nC
Q _{gs}	Gate-Source Charge		--	3	--	nC
Q _{gd}	Gate-Drain Charge		--	3.3	--	nC
Switching Characteristics						
T _d (on)	Turn-on Delay Time	V _{DD} =20V, I _D =20A, R _G =3Ω, V _{GS} =10V	--	5.6	--	ns
T _r	Turn-on Rise Time		--	47	--	ns
T _d (off)	Turn-Off Delay Time		--	15	--	ns
T _f	Turn-Off Fall Time		--	6.4	--	ns
Source- Drain Diode Characteristics@ T _j = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =20A, V _{GS} =0V	--	0.9	1.2	V
T _{rr}	Reverse Recovery Time	I _{sd} =20A, V _{GS} =0V di/dt=100A/μs	--	6.1	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.6	--	nC

NOTE: ① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax} , starting $T_j = 25^\circ\text{C}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 20A$, $V_{GS} = 10V$. Part not recommended for use above this value

③ The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C .

④ Pulse width $\leq 380\mu s$; duty cycles $\leq 2\%$

Typical Characteristics

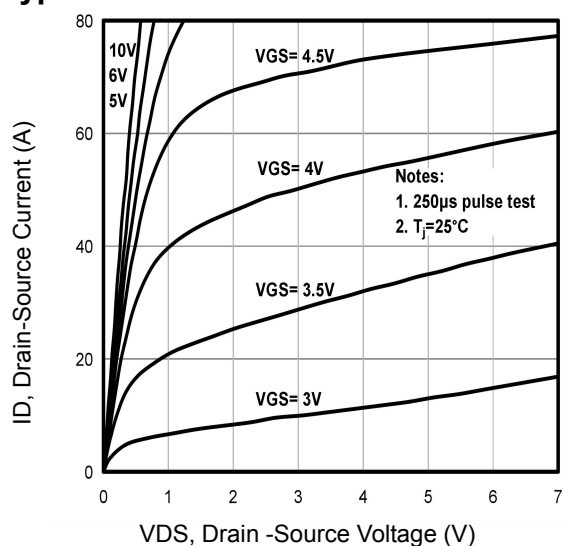


Fig1. Typical Output Characteristics

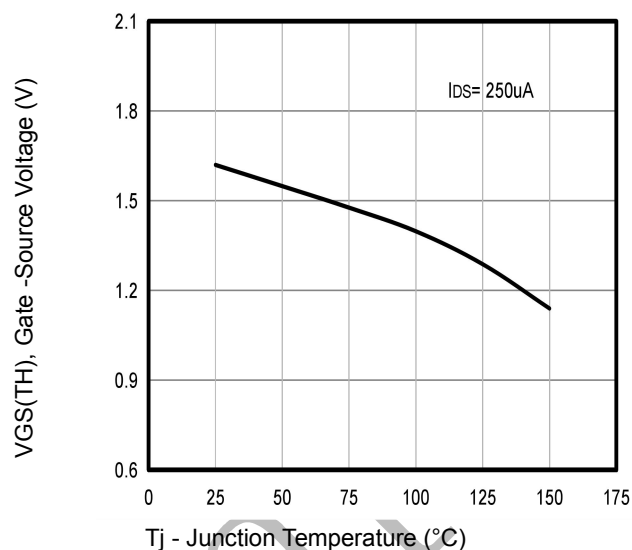


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

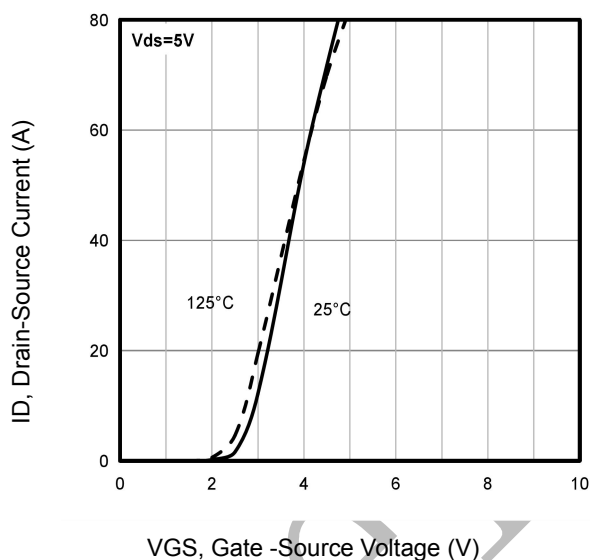


Fig3. Typical Transfer Characteristics

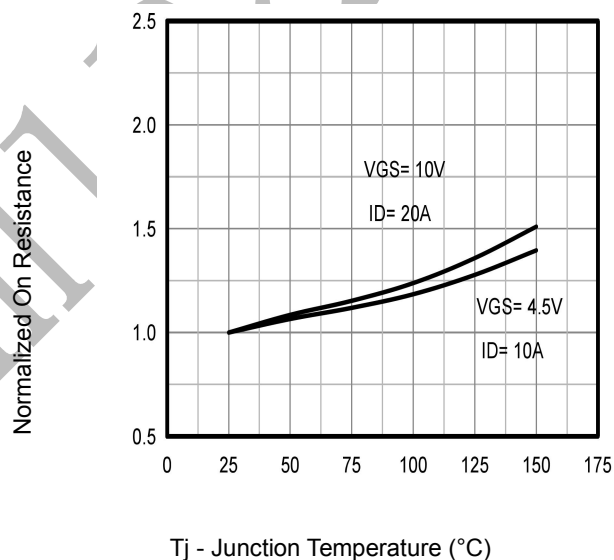


Fig4. Normalized On-Resistance Vs. T_j

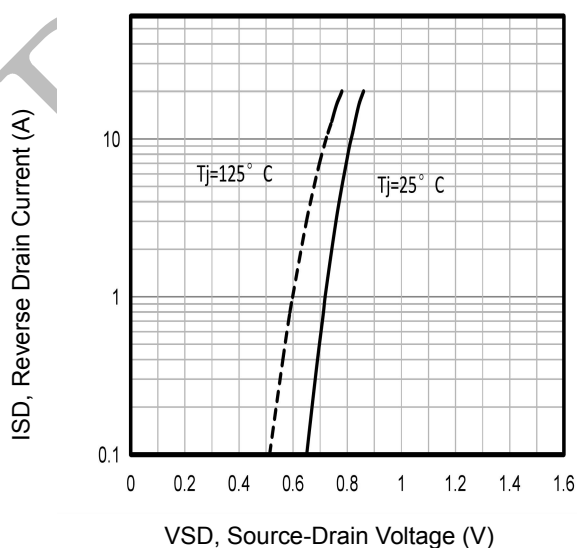


Fig5. Typical Source-Drain Diode Forward Voltage

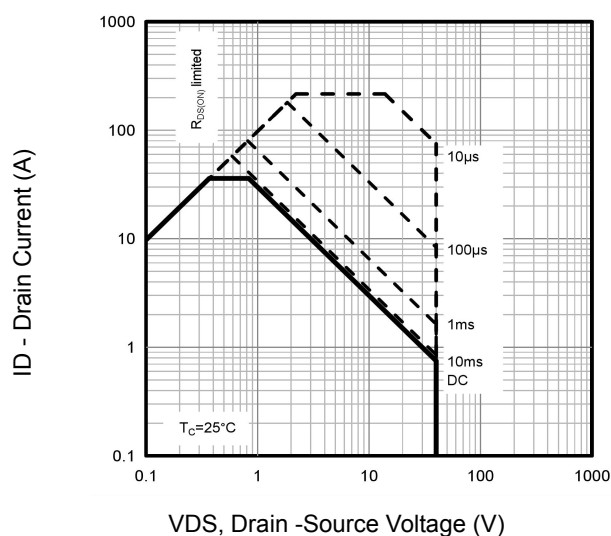


Fig6. Maximum Safe Operating Area

Typical Characteristics

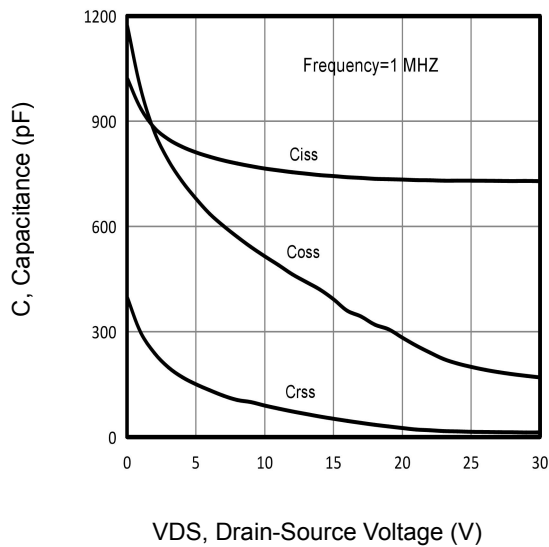


Fig7. Typical Capacitance Vs. Drain-Source Voltage

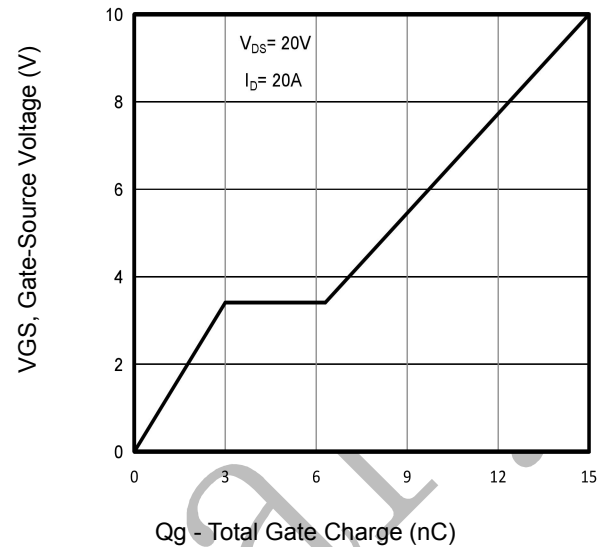


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

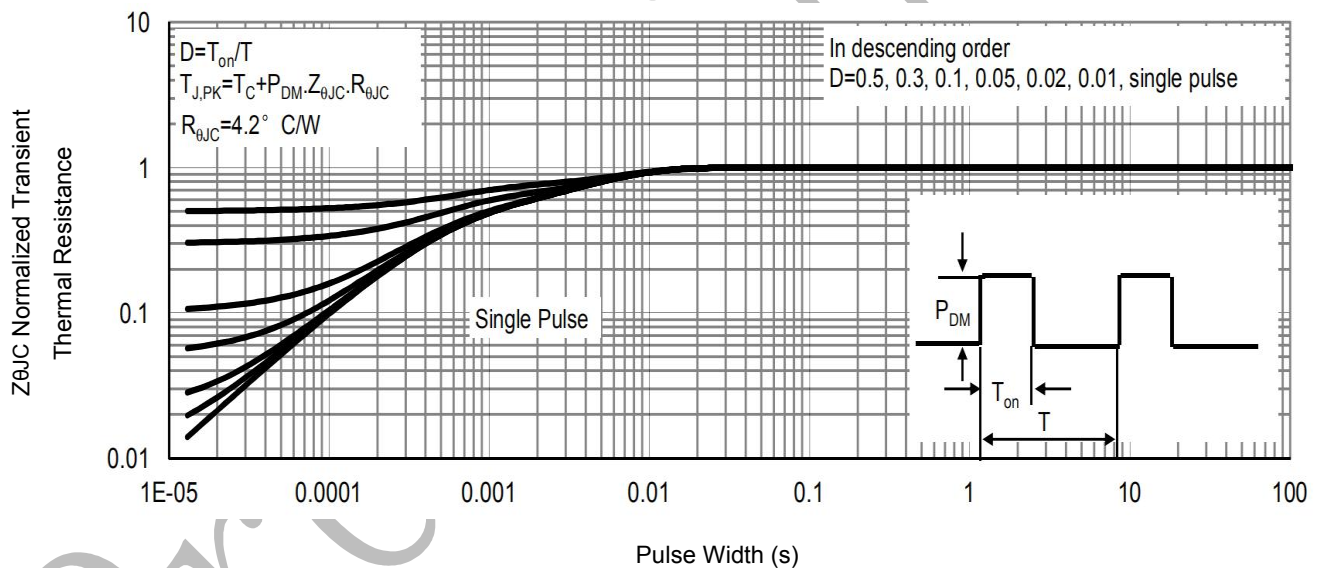


Fig9. Normalized Maximum Transient Thermal Impedance

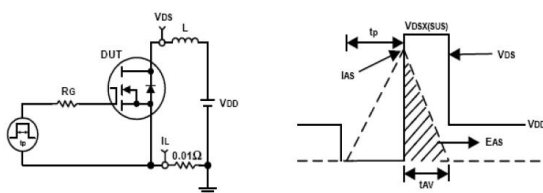


Fig10. Unclamped Inductive Test Circuit and waveforms

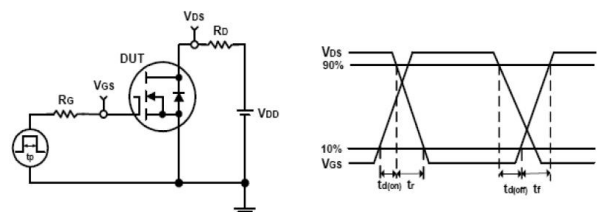
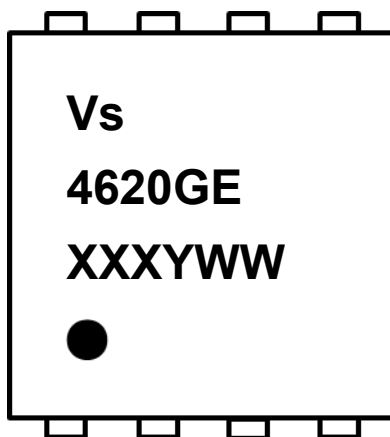


Fig11. Switching Time Test Circuit and waveforms

Marking Information



1st line: Vanguard Code (Vs)

2nd line: Part Number (4620GE)

3rd line: Date code (XXYYWW)

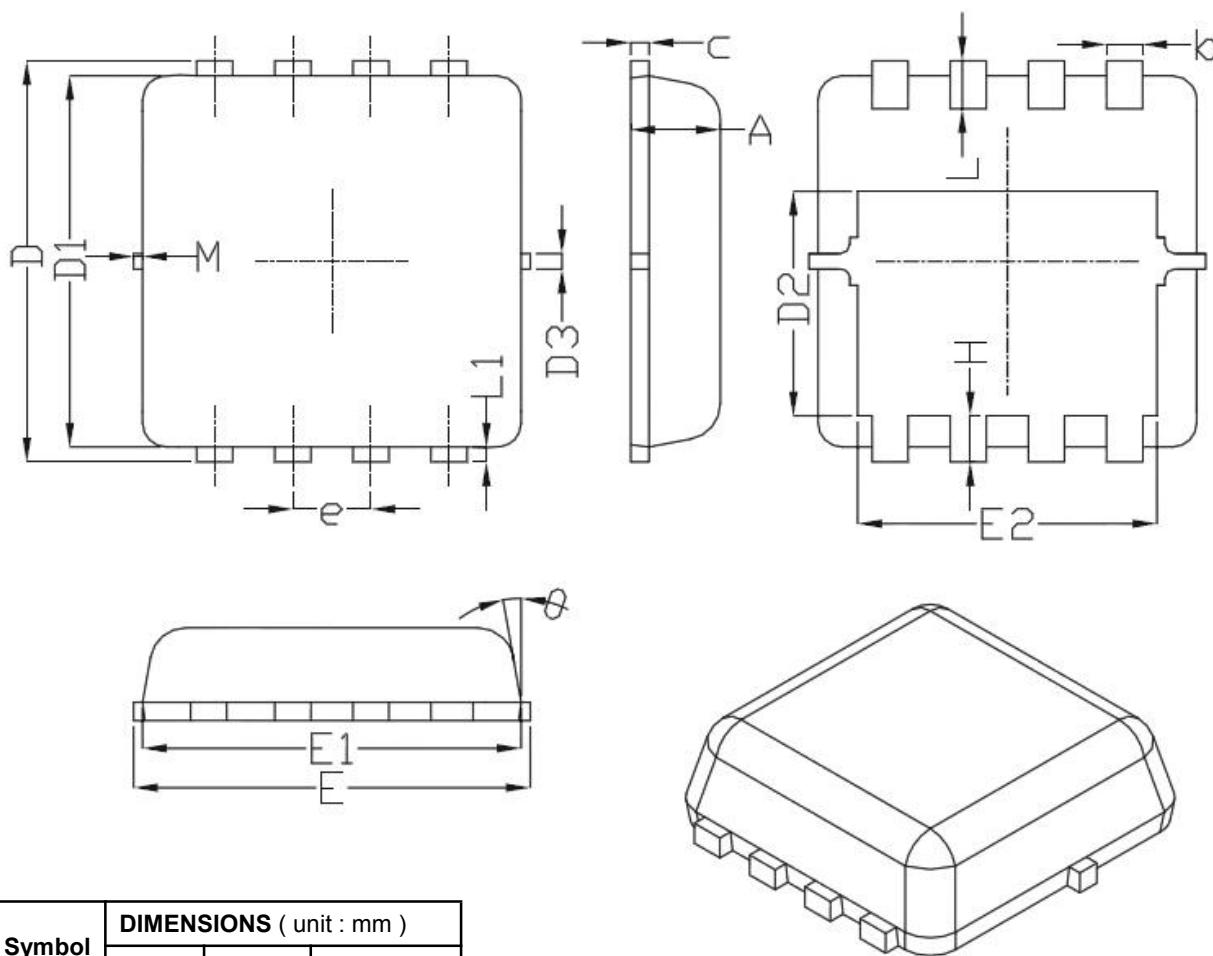
XXX: Wafer Lot Number Code , code changed with Lot Number

Y: Year Code , refer to table below

WW: Week Code (01 to 53)

Code	C	D	E	F	G	H	J	K	L	M	N	P	Q	R	S	T
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030

PDFN3333 Package Outline Data



Symbol	DIMENSIONS (unit : mm)		
	Min	Typ	Max
A	0.7	0.75	0.8
b	0.25	0.3	0.35
C	0.1	0.15	0.25
D	3.25	3.35	3.45
D1	3	3.1	3.2
D2	1.78	1.88	1.98
D3	--	0.13	--
E	3.2	3.3	3.4
E1	3	3.15	3.2
E2	2.39	2.49	2.59
e	0.65 BSC		
H	0.3	0.39	0.5
L	0.3	0.4	0.5
L1	--	0.13	--
θ	--	10°	12°
M	*	*	0.15
* Not specified			

Notes:

1. Follow JEDEC MO-240 variation CA.
2. Dimensions "D1" and "E1" do NOT include mold flash protrusions or gate burrs.
3. Dimensions "D1" and "E1" include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25mm per side.

Customer Service

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